

IN THE CLAIMS:

Claim 1. (currently amended): A semiconductor light emitting device comprising:

an active layer composed of a nitride based semiconductor;

a cladding layer formed on said active layer, composed of a nitride based semiconductor of a first conductivity type, and having a flat portion and a ridge portion formed on the flat portion; **and**

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a first current blocking layer formed on said flat portion and on sidewalls of said ridge portion of said cladding layer and composed of a high-resistive nitride based semiconductor containing impurities; and

- a second current blocking layer formed on said first current blocking layer and composed of a nitride based semiconductor of a second conductivity type opposite to said first conductivity type;

wherein the cladding layer is composed of AlGa_N; **and**

wherein the first current blocking layer is composed of AlGa_N having a larger Al composition ratio than that of the cladding layer; and

wherein said impurities contain at least one of zinc, beryllium, calcium, and carbon.

a second current blocking layer formed on said first current blocking layer and composed of a nitride based semiconductor of a second conductivity type opposite to said first conductivity type;

wherein the cladding layer is composed of AlGa_N;

wherein the first current blocking layer is composed of AlGa_N having a larger Al composition ratio than that of the cladding layer; **and**

wherein said impurities contain at least one of zinc, beryllium, calcium, and carbon.

Claim 2 (cancelled)

Claim 3 (original): The semiconductor light emitting device according to claim 1, wherein said first current blocking layer has a resistance value of not less than $1.5 \Omega \cdot \text{cm}$

Claim 4 (cancelled)

Claim 5 (original): The semiconductor light emitting device according to claim 1, wherein the thickness of said first current blocking layer is not less than $0.5 \mu\text{m}$.

Claim 6 (original): The semiconductor light emitting device according to claim 5, wherein the thickness of said first current blocking layer is not less than $1.0 \mu\text{m}$.

Claim 7 (original): The semiconductor light emitting device according to claim 1, wherein the thickness of the flat portion of said cladding layer is not more than $0.3 \mu\text{m}$.

Claim 8 (original): The semiconductor light emitting device according to claim 7, wherein the thickness of the flat portion of said cladding layer is not more than $0.08 \mu\text{m}$.

Claim 9 (original): The semiconductor light emitting device according to claim 1, wherein said nitride based semiconductor contains at least one of boron, gallium, aluminum, indium, and thallium.

31
Claim 10 (currently amended): A semiconductor light emitting device comprising:
an active layer composed of a nitride based semiconductor;
a cladding layer formed on said active layer, composed of a nitride based semiconductor of
a first conductivity type, and having a flat portion and a ridge portion formed on the flat portion; and
a first current blocking layer formed on said flat portion and on sidewalls of said ridge
portion of said cladding layer and composed of a high-resistive nitride based semiconductor
containing impurities; and
a second current blocking layer formed on said first current blocking layer and composed of
a nitride based semiconductor of a second conductivity type opposite to said first conductivity type;
wherein the cladding layer is composed of AlGa_N; and
wherein the first current blocking layer is composed of AlGa_N having a larger Al
composition ratio than that of the cladding layer;
wherein said first current blocking layer is composed of a high-resistive nitride based
semiconductor containing impurities; and
wherein said impurities contain at least one of zinc, beryllium, calcium, and carbon.

Claim 11 (cancelled)

Claim 12 (cancelled)

Claim 13 (original): The semiconductor light emitting device according to claim 10, wherein said first current blocking layer has a resistance value of not less than $1.5 \Omega\cdot\text{cm}$.

Claim 14 (cancelled):

Claim 15 (original): The semiconductor light emitting device according to claim 10, wherein the thickness of said first current blocking layer is not less than $0.5 \mu\text{m}$.

Claim 16 (original): The semiconductor light emitting device according to claim 15, wherein the thickness of said first current blocking layer is not less than $1.0 \mu\text{m}$.

Claim 17 (original): The semiconductor light emitting device according to claim 10, wherein the thickness of the flat portion of said cladding layer is not more than $0.3 \mu\text{m}$.

Claim 18 (original): The semiconductor light emitting device according to claim 17, wherein the thickness of the flat portion of said cladding layer is not more than $0.08 \mu\text{m}$.

Claim 19 (original): The semiconductor light emitting device according to claim 10, said nitride based semiconductor contains at least one of boron, gallium, aluminum, indium, and thallium.
